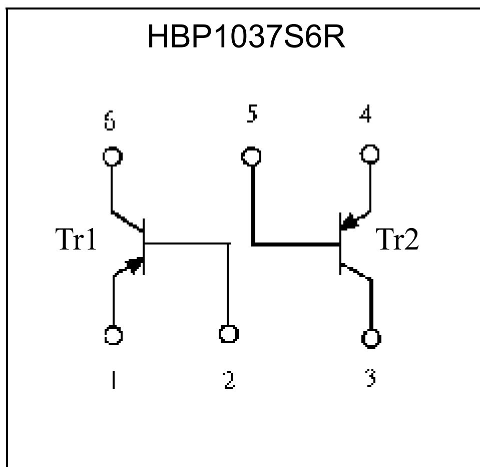
General Purpose PNP Epitaxial Planar Transistors (dual transistors)

HBP1037S6R

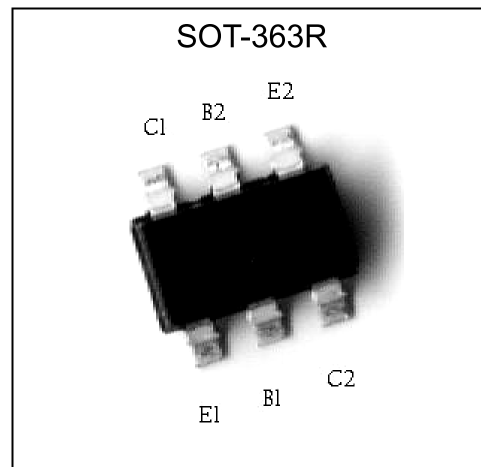
Features

- Two BTA1037 chips in a SOT-363R package.
- Mounting possible with SOT-323 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.
- Excellent h_{FE} linearity
- Complementary to HBN2412S6R.
- Pb-free lead plating and halogen-free package.

Equivalent Circuit

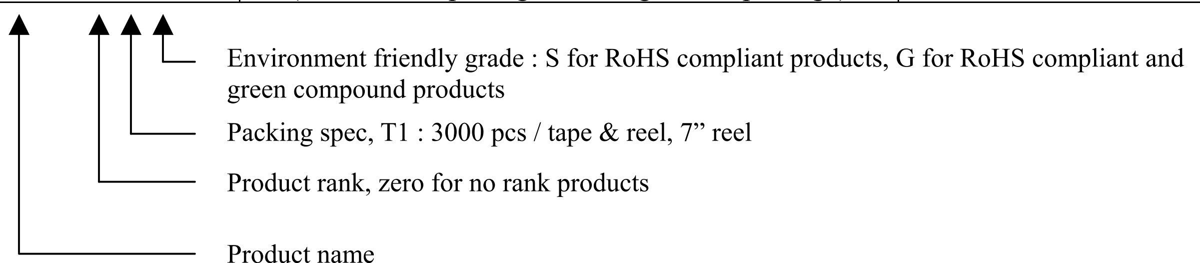


Outline



Ordering Information

Device	Package	Shipping
HBP1037S6R-0-T1-G	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel



The following characteristics apply to both Tr1 and Tr2

Absolute Maximum Ratings (Ta=25°C, each transistor)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-65	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-150	mA
Power Dissipation	Pd	200(total) *1	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating Junction Temperature Range	Tj	-55~+150	°C
Storage Temperature Range	Tstg	-55~+150	°C

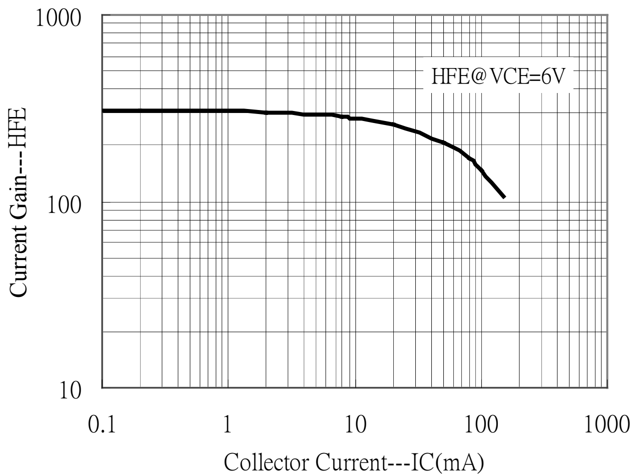
Note : *1 150mW per element must not be exceeded

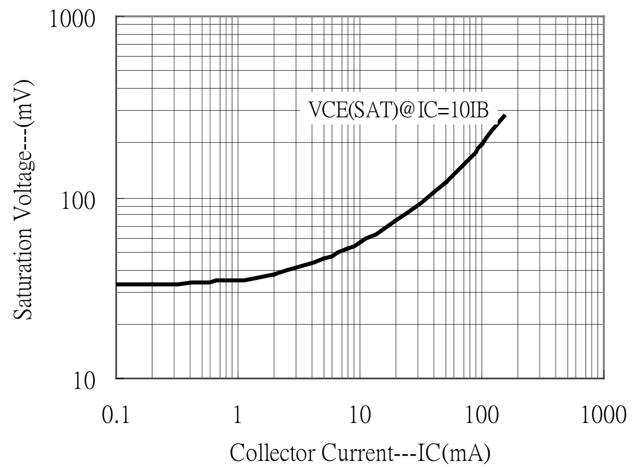
Characteristics (Ta=25°C, each transistor)

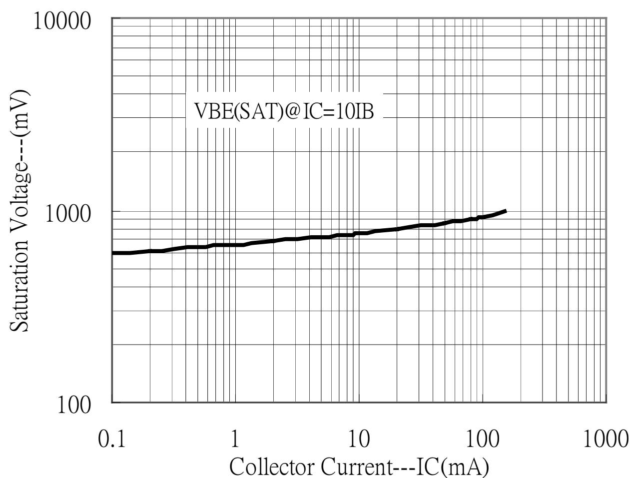
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-100	-	-	V	I_C=-50μA
BV_{CEO}	-65	-	-	V	I_C=-1mA
BV_{EBO}	-6	-	-	V	I_E=-50μA
I_{CBO}	-	-	-0.1	μA	V_{CB}=-80V
I_{EBO}	-	-	-0.1	μA	V_{EB}=-6V
*$V_{CE(sat)}$	-	-	-0.2	V	I_C=-10mA, I_B=-0.5mA
*$V_{CE(sat)}$	-	-0.12	-0.3	V	I_C=-50mA, I_B=-5mA
*$V_{CE(sat)}$	-	-	-0.4	V	I_C=-100mA, I_B=-5mA
V_{BE}	-0.6	-	-0.7	V	V_{CE}=-6V, I_C=-2mA
V_{BE}	-	-	-0.76	V	V_{CE}=-6V, I_C=-10mA
*h_{FE}	200	-	450		V_{CE}=-6V, I_C=-1mA
f_T	80	110	-	MHz	V_{CE}=-10V, I_C=-1mA, f=100MHz
Cob	-	2	3.5	pF	V_{CB}=-10V, f=1MHz

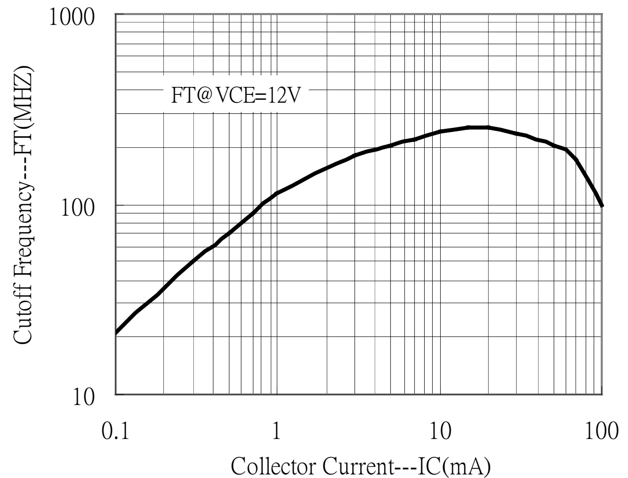
*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

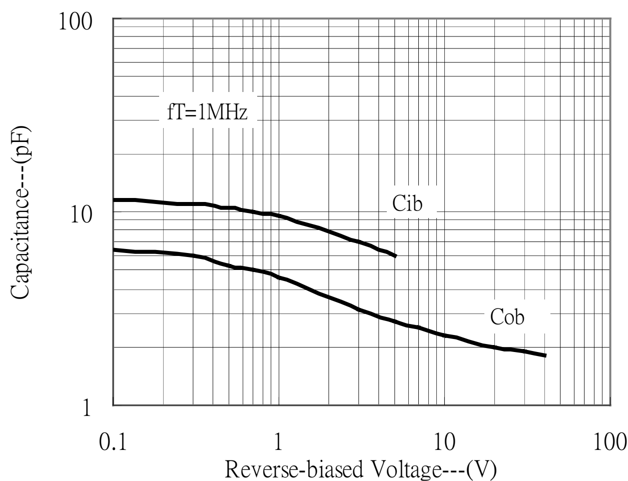
Typical Characteristics

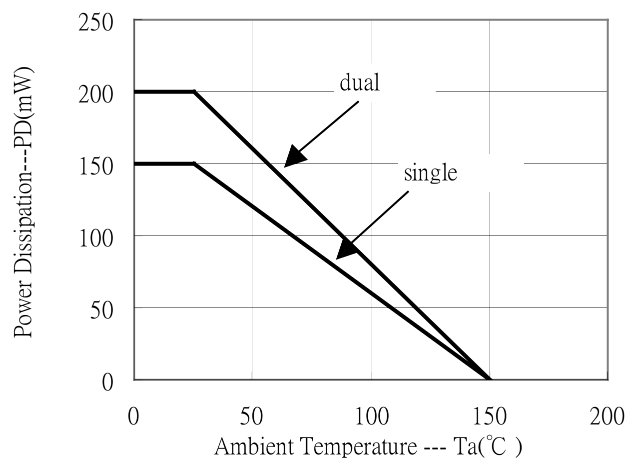




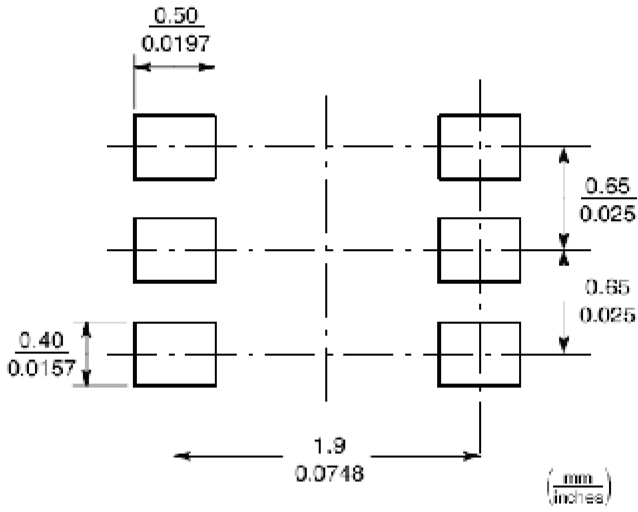




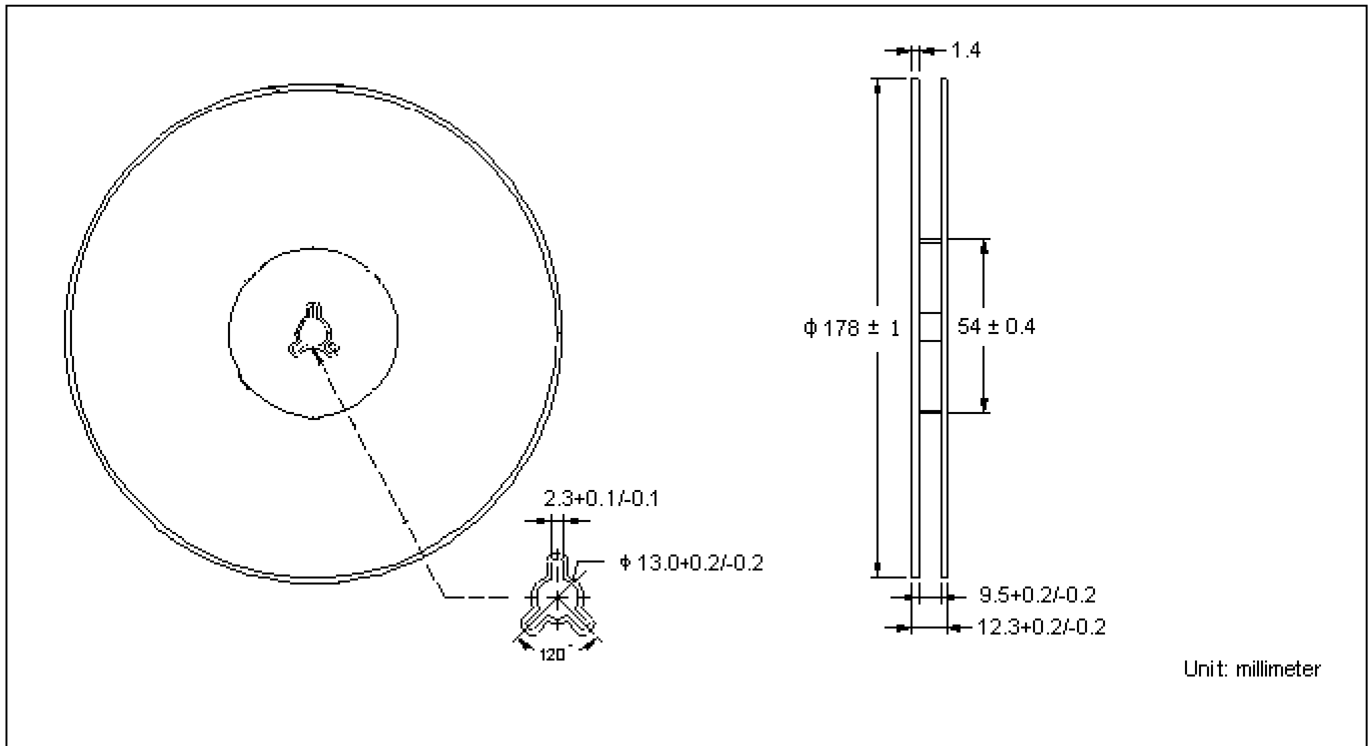




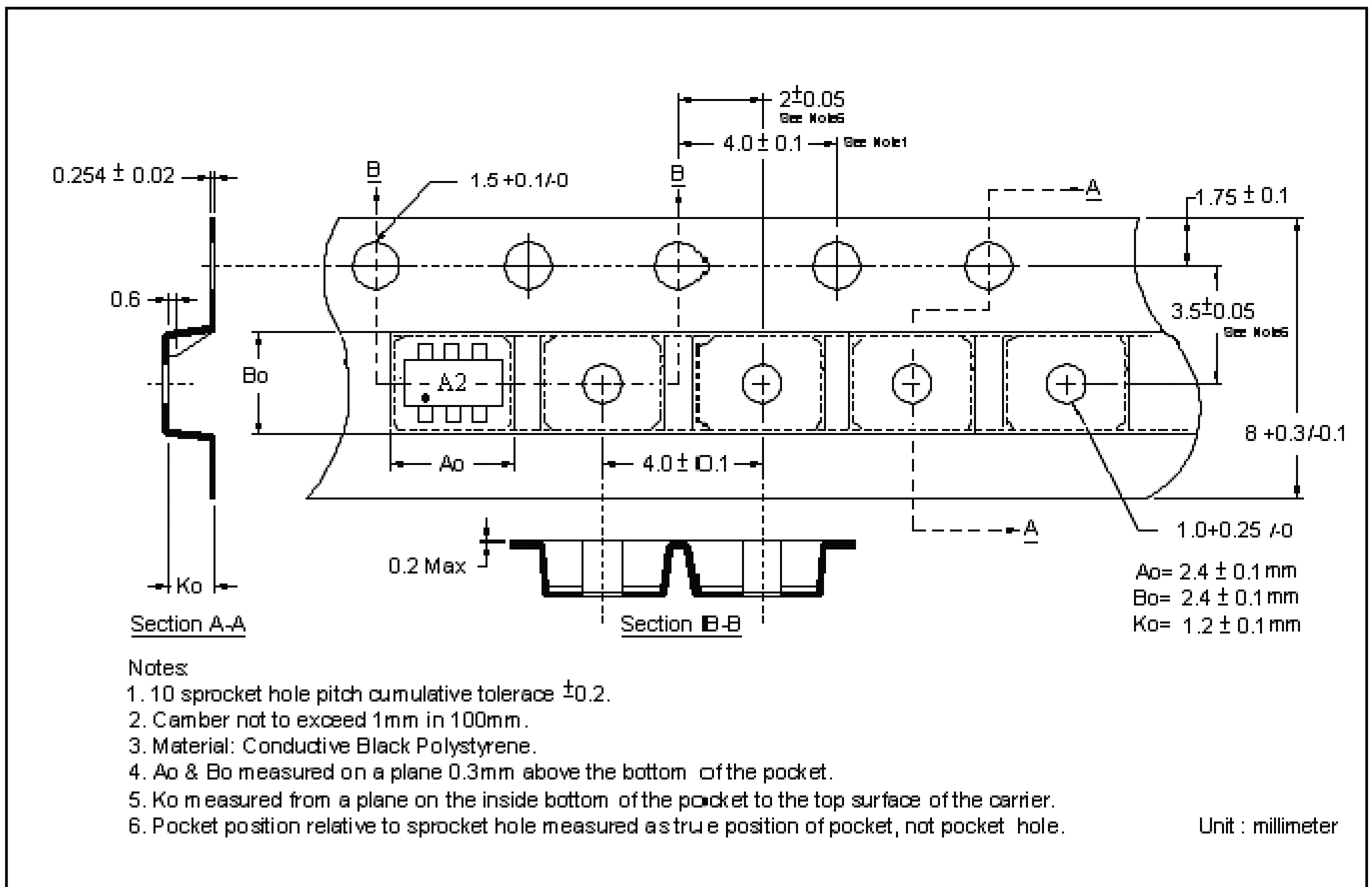
Recommended Soldering Footprint



Reel Dimension



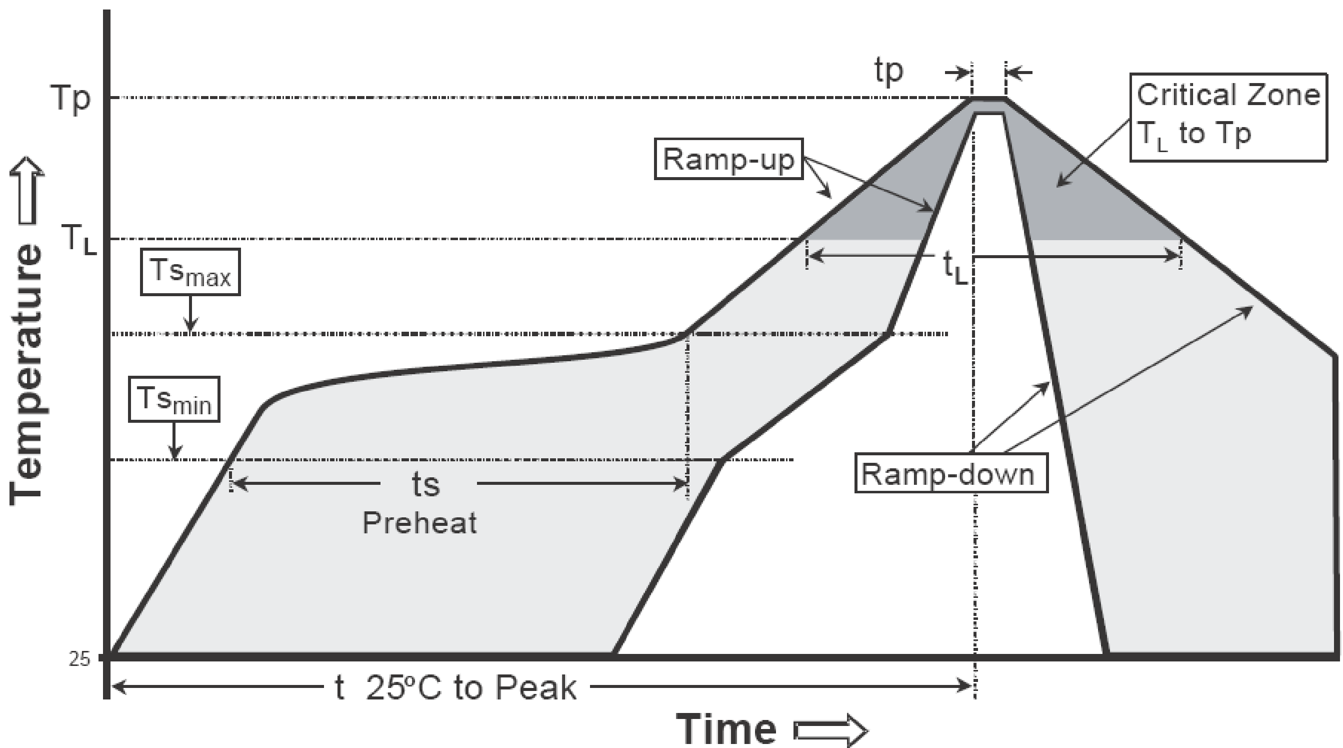
Carrier Tape Dimension



Recommended wave soldering condition

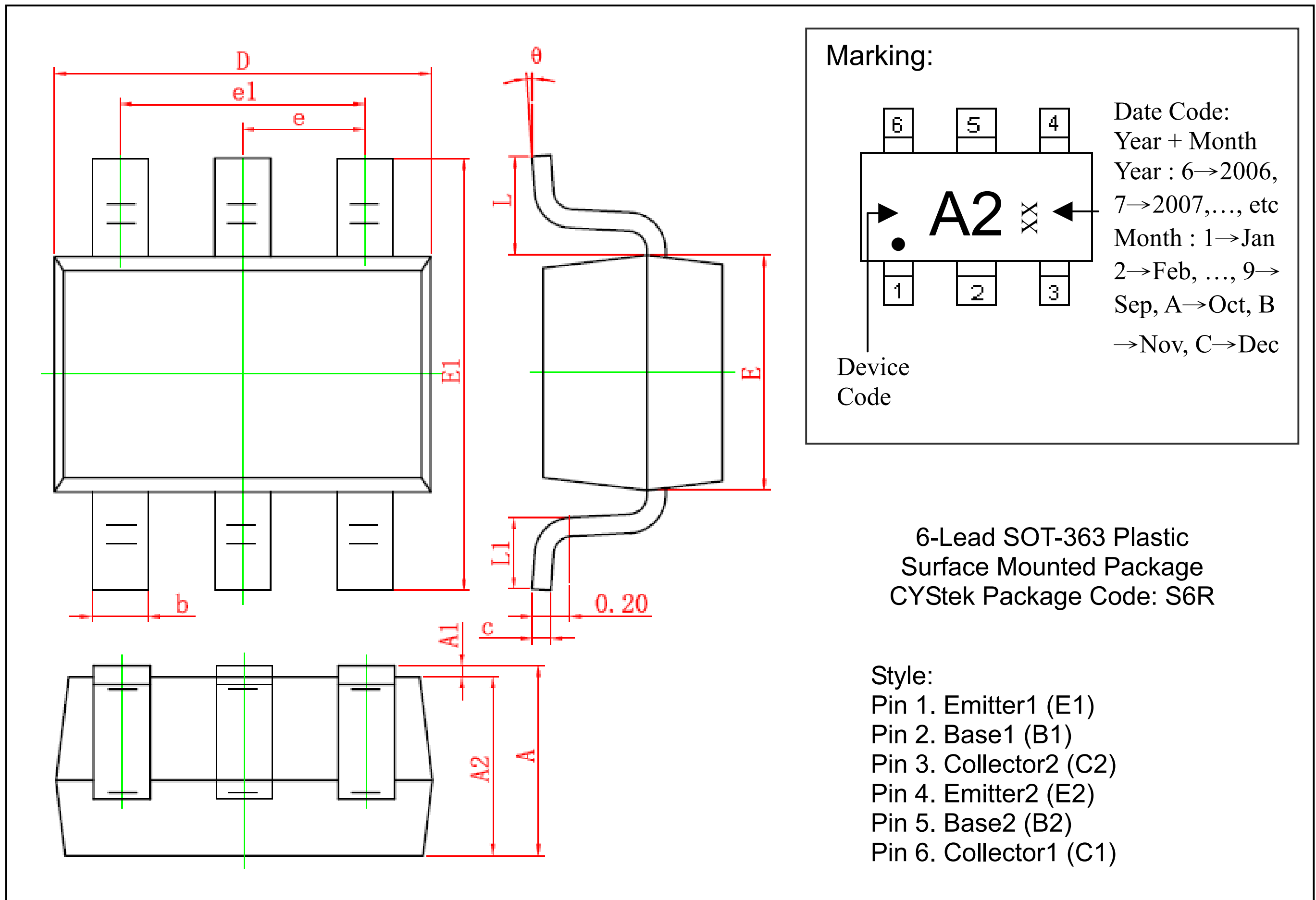
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time(t_s min to t_s max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

SOT-363 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

Notes : 1.Controlling dimension : millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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